

Features

- VDS = 20V
- RDS(ON) = 300mΩ (typ.) @ VGS= 2.5V
- RDS(ON) = 250mΩ (typ.) @ VGS= 4.5V
- ESD Protected up to 2KV

Application

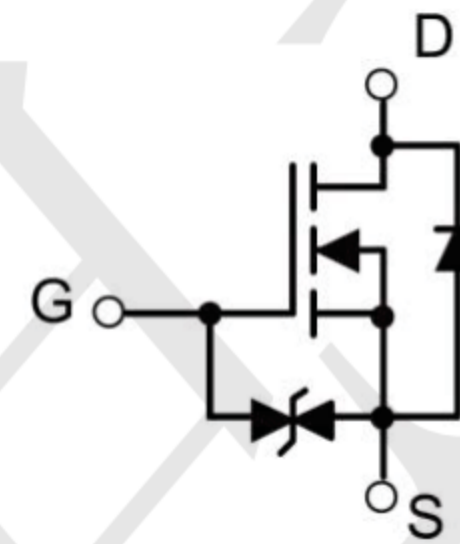
- Load/Power Switching
- Interfacing Switching
- Battery Management for Ultra Small Portable Electronics
- Logic Level Shift

Package and Pin Configuration



SOT323

Circuit diagram



Marking: 21P

Absolute Maximum Ratings (T_A=25°C unless otherwise noted)

TECH PUBLIC Parameter	Symbol	Value	Unit
Drain-Source Voltage	V _{DS}	20	V
Gate-Source Voltage	V _{GS}	±8	V
Continuous Drain Current	I _D	0.9	A
Pulsed Drain Current (t=300μs) ⁽¹⁾	I _{DM}	1.5	A
Power Dissipation ⁽²⁾	P _D	0.35	W
Thermal Resistance from Junction to Ambient	R _{θJA}	357	°C/W
Junction Temperature	T _J	150	°C
Storage Temperature	T _{STG}	-55~ +150	°C

Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

TECH PUBLIC Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Static Characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	20	25		V
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 20V, V_{GS} = 0V$			1	μA
Gate-body leakage current	I_{GSS}	$V_{GS} = \pm 18V, V_{DS} = 0V$			± 10	μA
Gate threshold voltage ⁽³⁾	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	0.5	0.7	1.1	V
Drain-source on-resistance ⁽³⁾	$R_{DS(on)}$	$V_{GS} = 4.5V, I_D = 500mA$		250	400	m Ω
		$V_{GS} = 2.5V, I_D = 500mA$		300	500	
Forward tranconductance	g_{FS}	$V_{DS} = 10V, I_D = 500mA$			1.2	S
Dynamic characteristics⁽⁴⁾						
Input Capacitance	C_{iss}	$V_{DS} = 10V, V_{GS} = 0V, f = 1MHz$		45		pF
Output Capacitance	C_{oss}			9		
Reverse Transfer Capacitance	C_{rss}			6		
Switching Characteristics⁽⁴⁾						
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 10V, I_D = 500mA,$ $V_{GS} = 4.5V, R_G = 6\Omega$		20		ns
Turn-on rise time	t_r			90		
Turn-off delay time	$t_{d(off)}$			750		
Turn-off fall time	t_f			400		
Source-Drain Diode characteristics						
Diode Forward voltage ⁽³⁾	V_{DS}	$I_S = 0.15A, V_{GS} = 0V$			1.3	V

Characteristic Curves

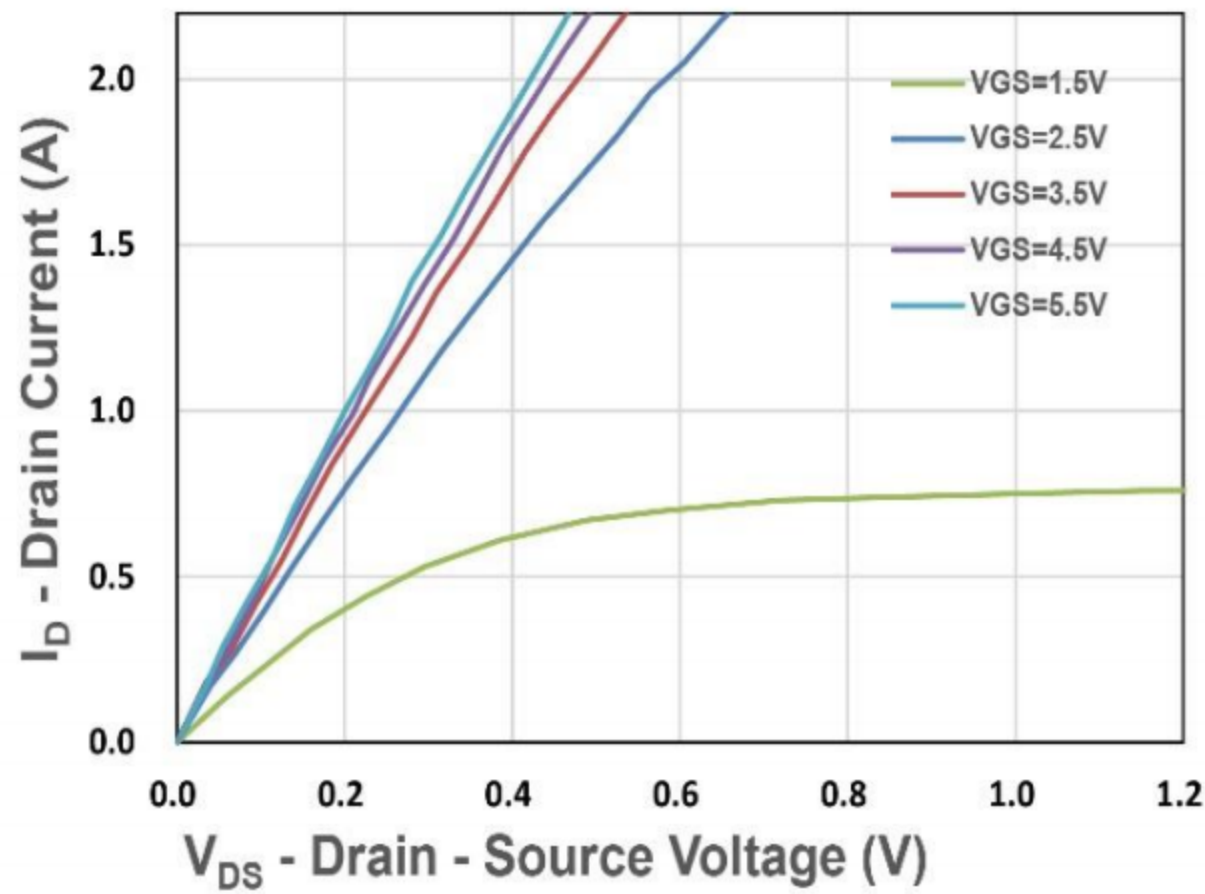


Figure 1. Output Characteristics

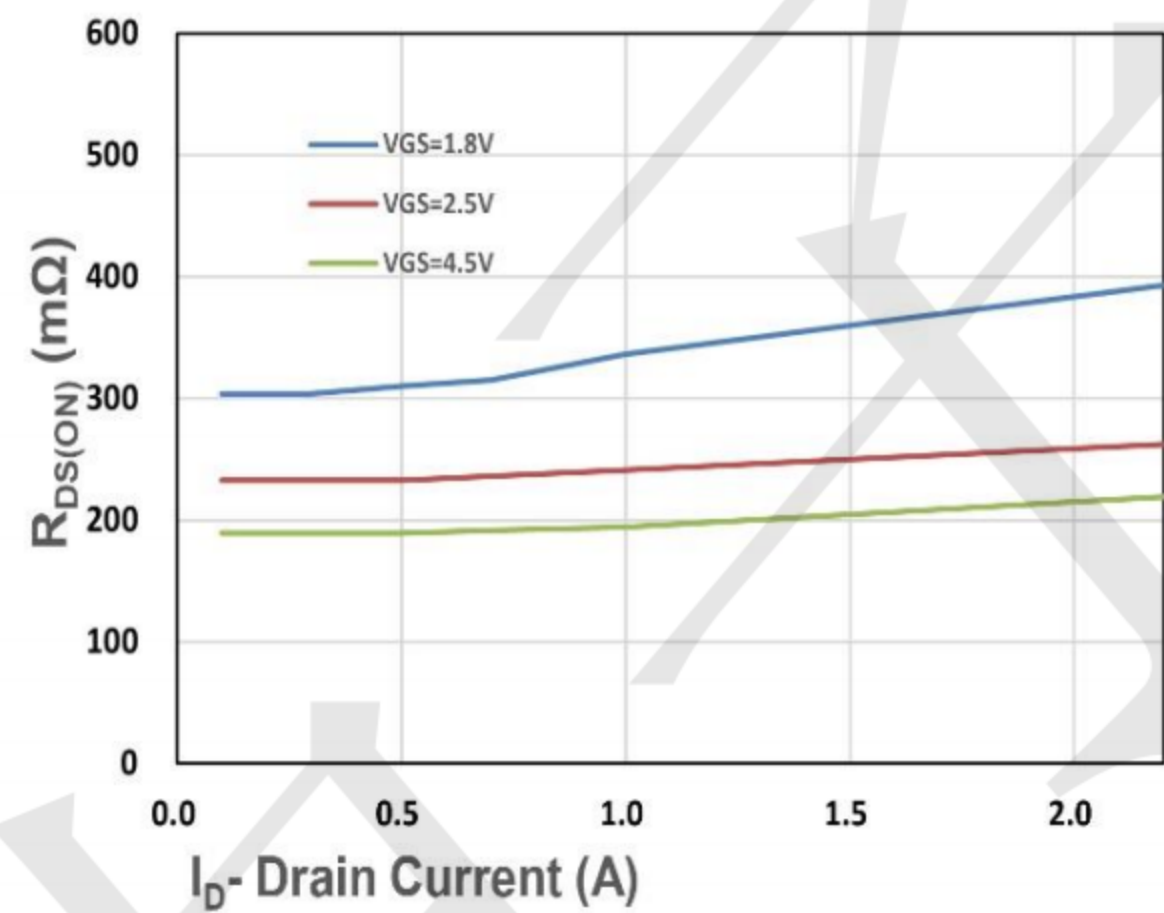


Figure 2. On-Resistance vs. I_D

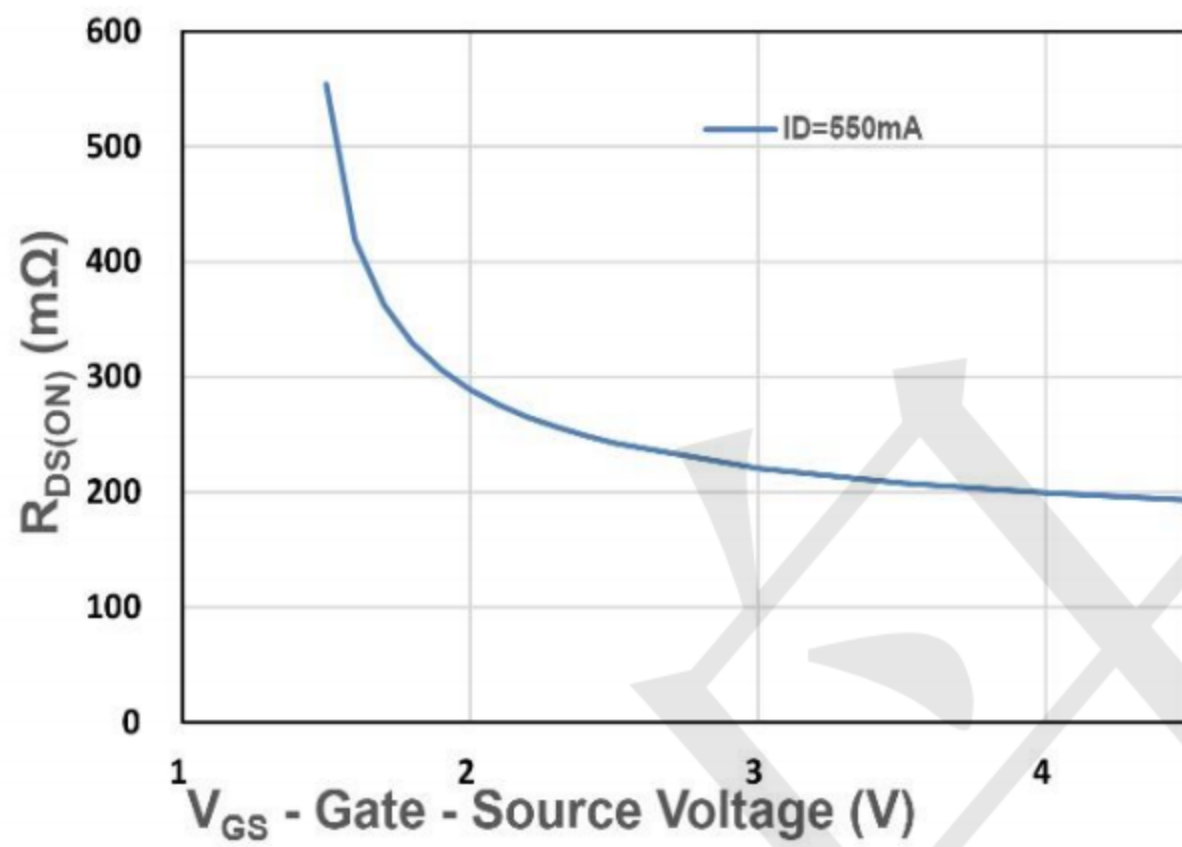


Figure 3. On-Resistance vs. V_{GS}

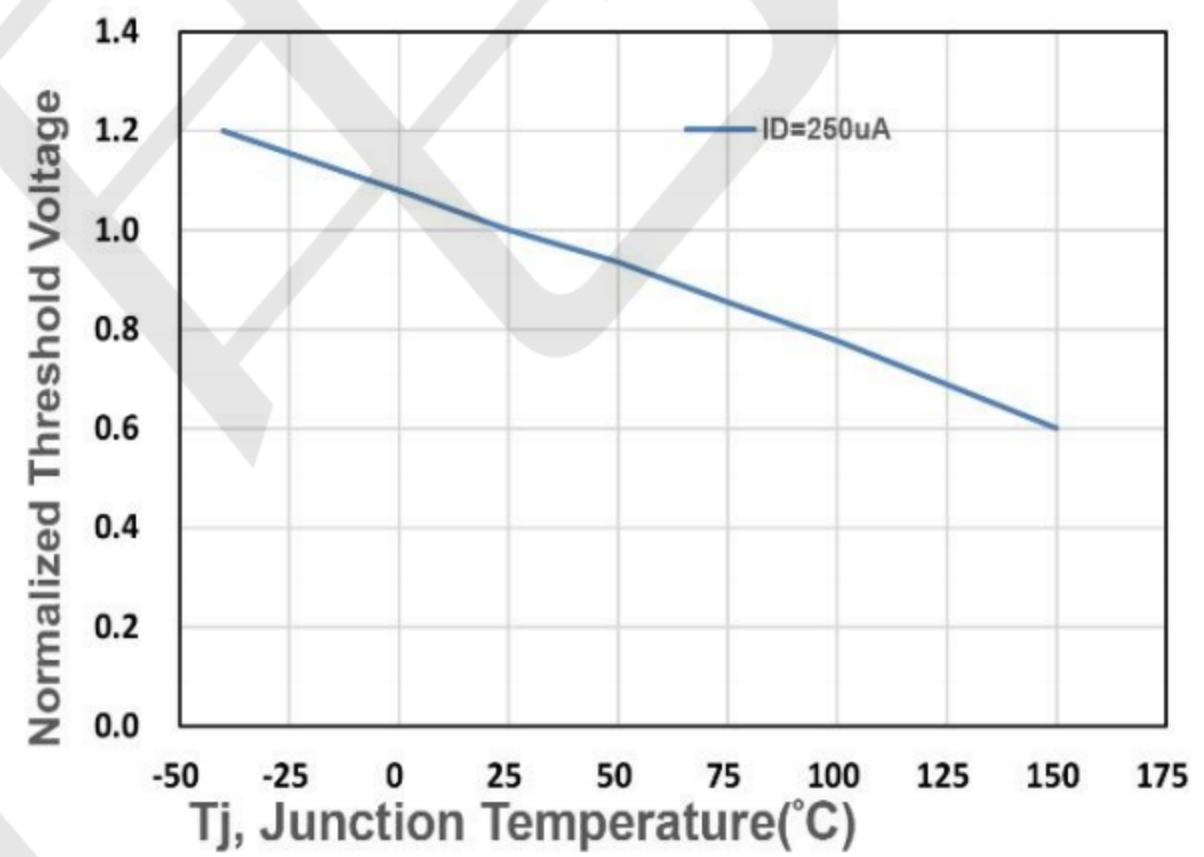


Figure 4. Gate Threshold Voltage

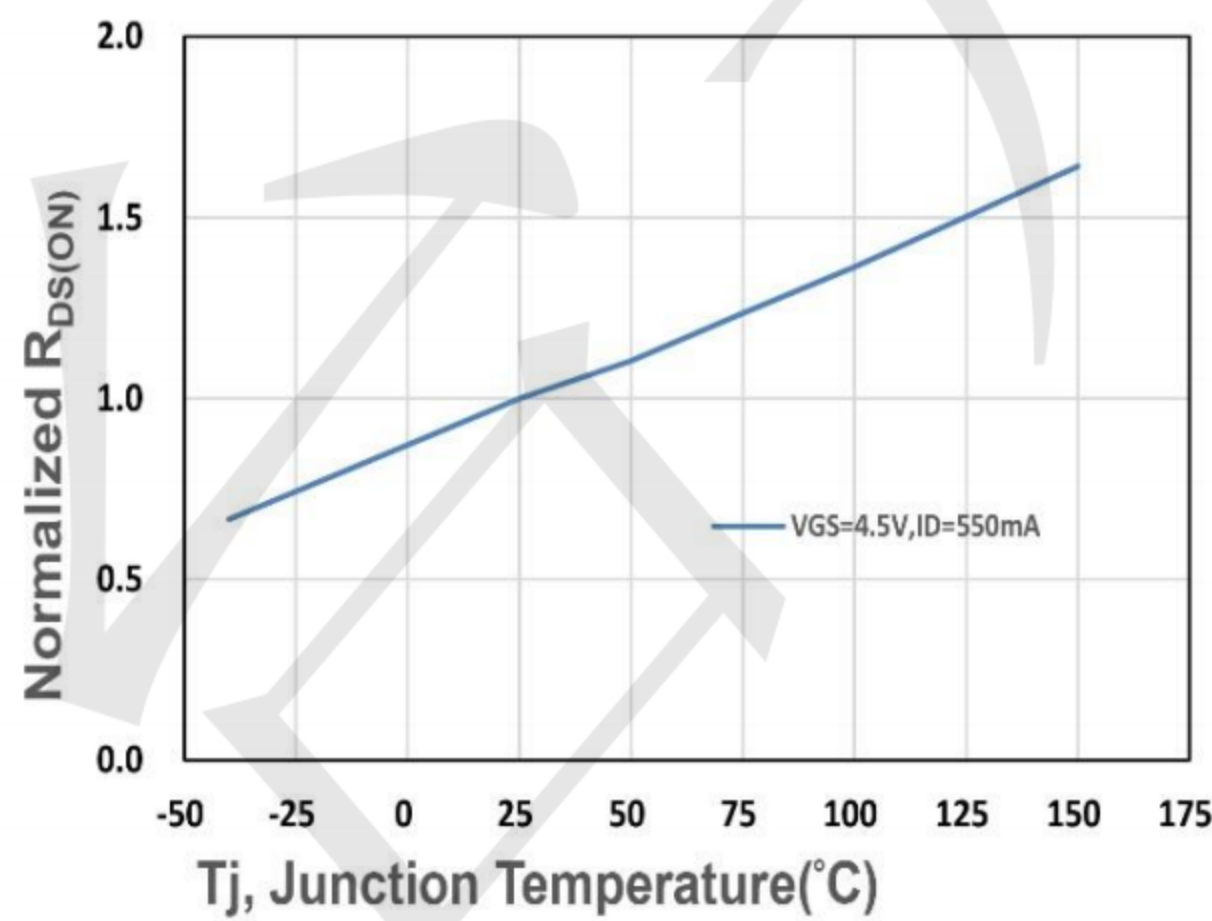


Figure 5. Drain-Source On Resistance

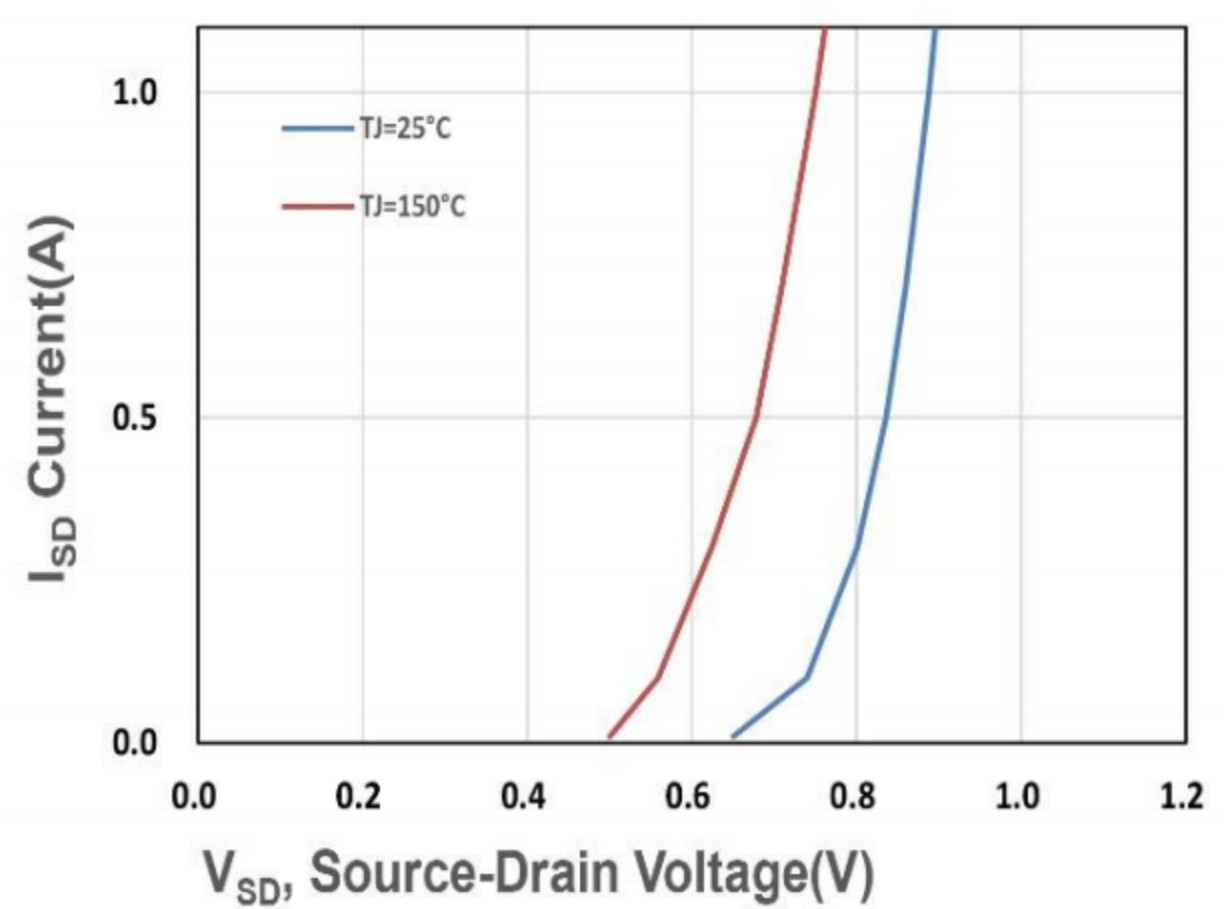


Figure 6. Source-Drain Diode Forward

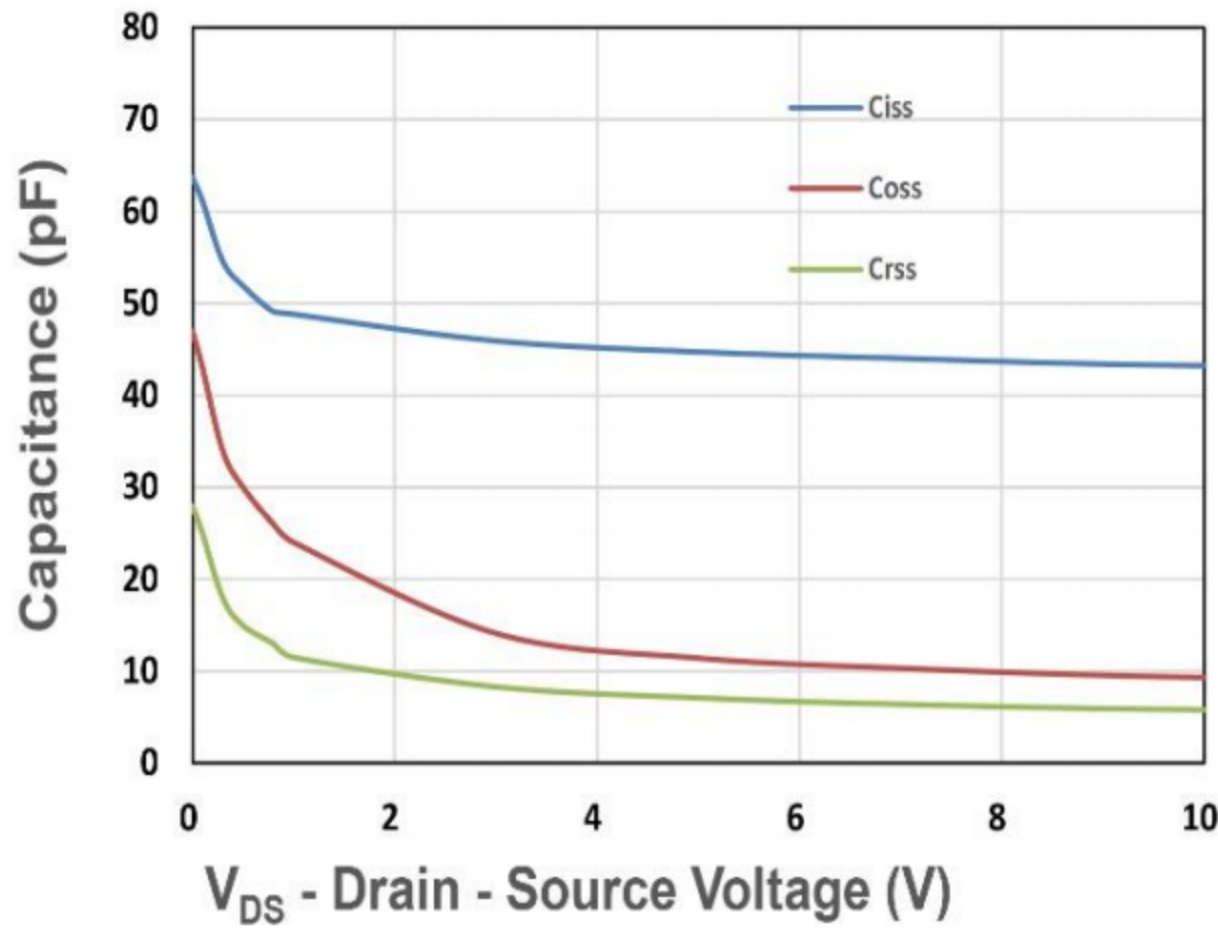


Figure 7. Capacitance

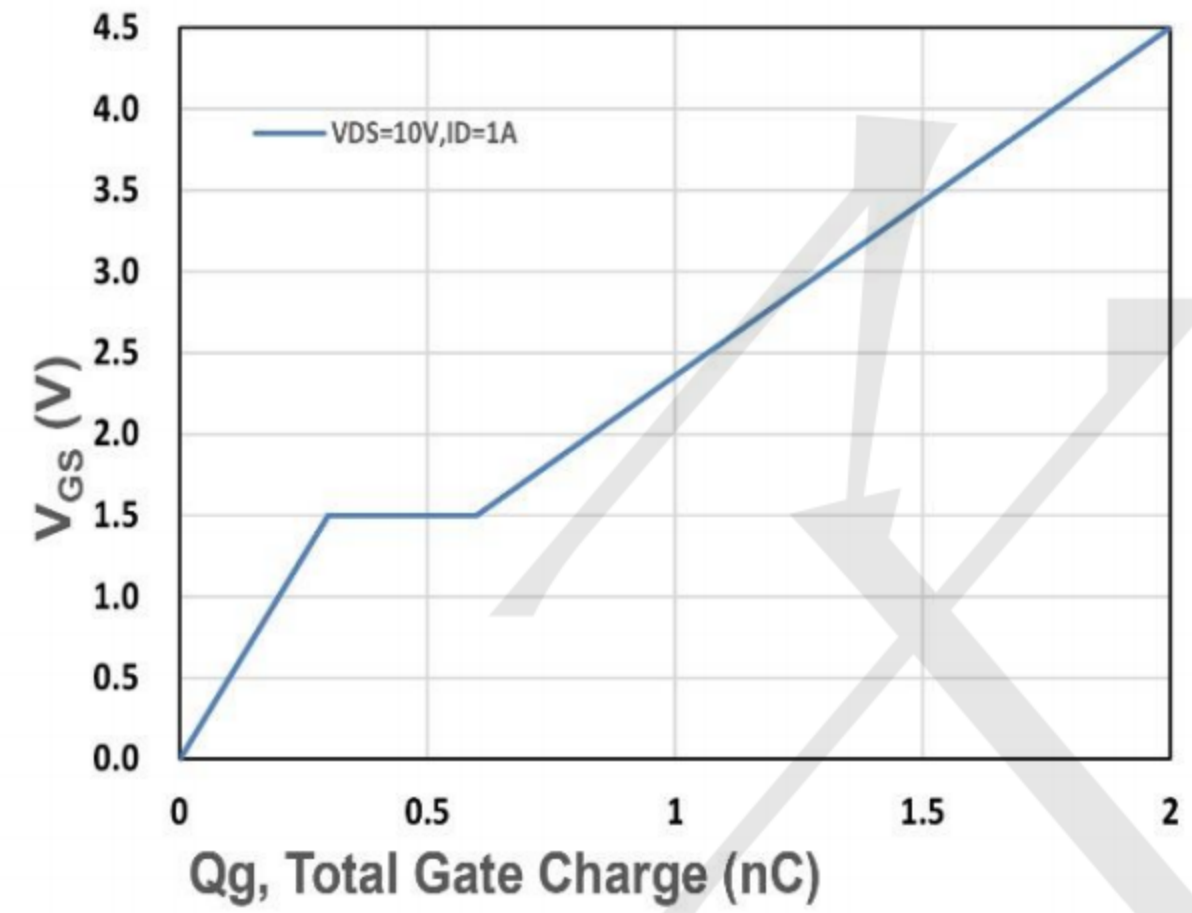


Figure 8. Gate Charge Characteristics

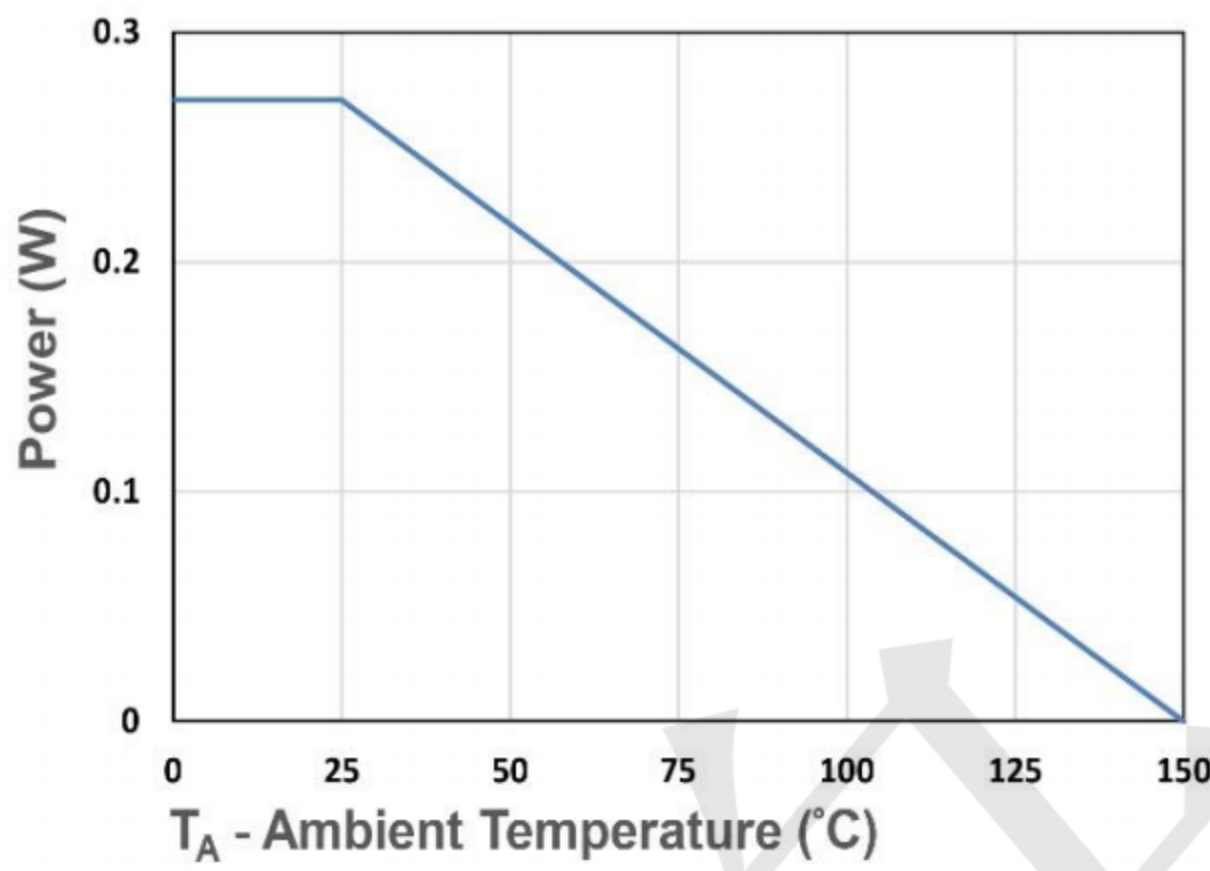


Figure 9. Power Dissipation

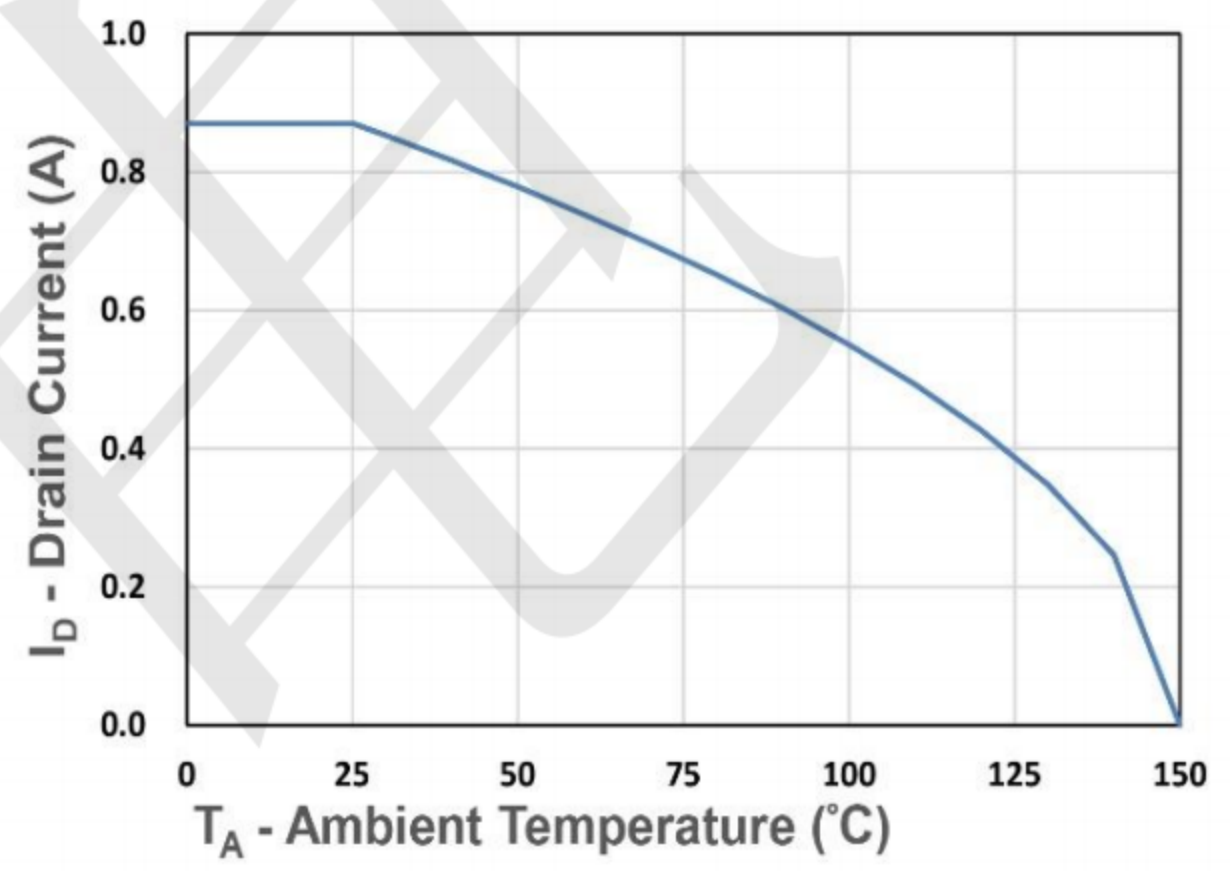


Figure 10. Drain Current

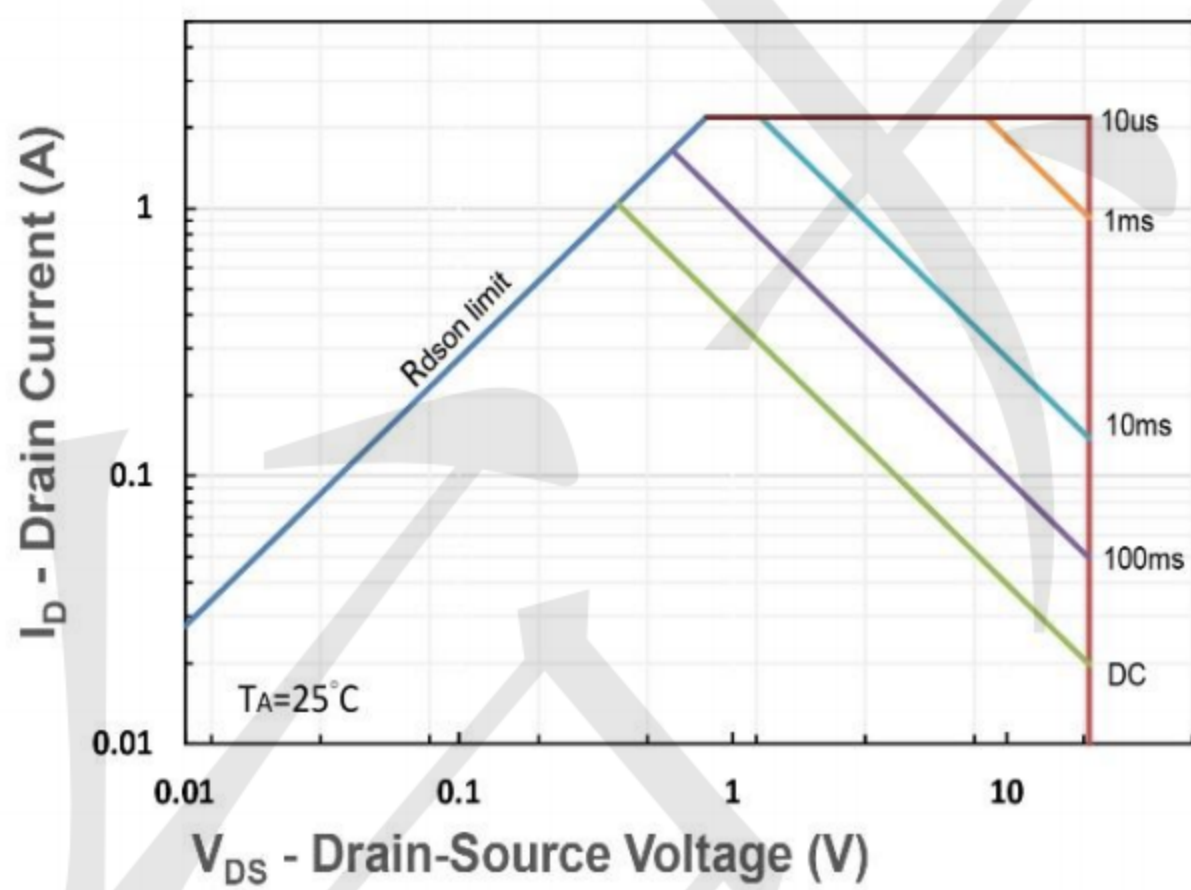


Figure 11. Safe Operating Area

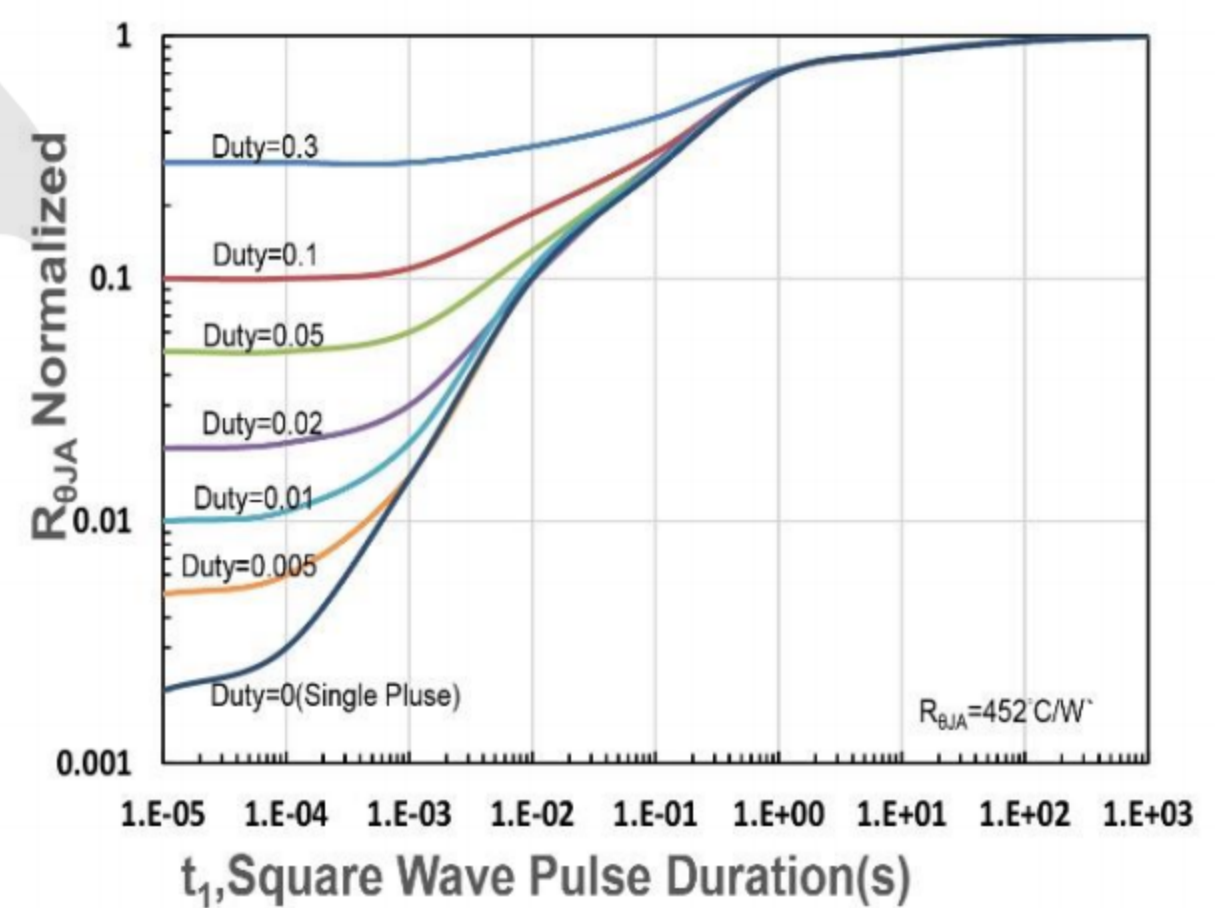
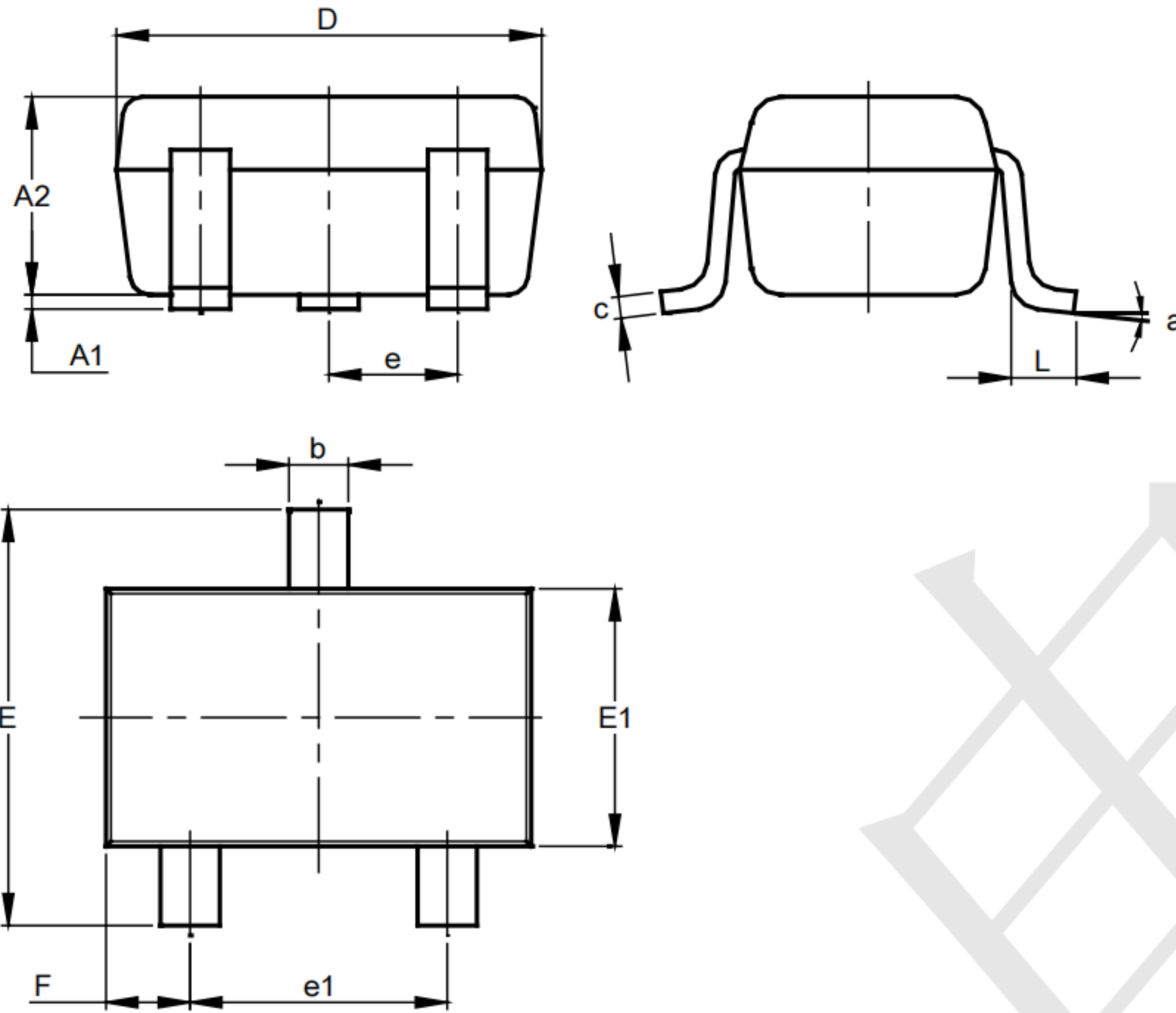


Figure 12. $R_{\theta JA}$ Transient Thermal Impedance

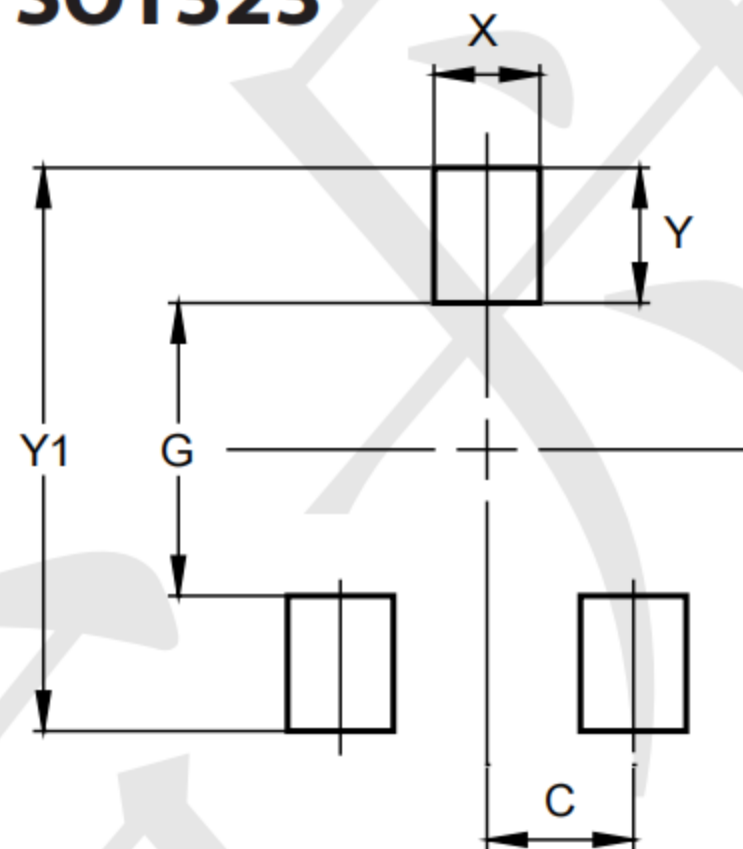


Outline Drawing - SOT323(SC70-3)



SOT323			
Dim	Min	Max	Typ
A1	0.00	0.10	0.05
A2	0.90	1.00	0.95
b	0.25	0.40	0.30
c	0.10	0.18	0.11
D	1.80	2.20	2.15
E	2.00	2.20	2.10
E1	1.15	1.35	1.30
e	0.650 BSC		
e1	1.20	1.40	1.30
F	0.375	0.475	0.425
L	0.25	0.40	0.30
a	0°	8°	--
All Dimensions in mm			

Land Pattern - SOT323



Dimensions	Value (in mm)
C	0.650
G	1.300
X	0.470
Y	0.600
Y1	2.500